

IN THE CLAIMS:

The following is a complete listing of the claims in this application, reflects all changes currently being made to the claims, and replaces all earlier versions and all earlier listings of the claims:

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1. (Currently amended) A sensor integrated on a single semiconductor substrate, comprising:

a sensor block including a pixel unit and a scanning unit for selecting a pixel of said the pixel unit, said the pixel unit comprising a plurality of pixels each including a light-receiving element;

a signal processing block for processing a signal output from said sensor block; and

a single electric power voltage input terminal for externally inputting an electric power voltage from outside of the sensor; and

means for setting a control circuit for generating a plurality of different voltages from the electric power voltage externally input at the single electric power voltage input terminal to make a power supply voltage or an amplitude or high level of a clock signal used in said sensor block to be higher than a power supply voltage of said signal processing block.

2. (Original) A sensor according to claim 1, wherein a gate insulating layer of at least some insulated gate transistors of said sensor block is thicker than that of an insulated gate transistor used in said signal processing block.

3. (Original) A sensor according to claim 1, wherein a well density of at least some insulated gate transistors of said sensor block is lower than that of an insulated gate transistor used in said signal processing block.

4. (Original) A sensor according to claim 1, wherein a threshold voltage of at least some insulated gate transistors of said sensor block is higher than that of an insulated gate transistor used in said signal processing block.

5. (Currently Amended) A sensor according to claim 1, wherein said the light-receiving element is a buried photodiode.

6. (Currently amended) A sensor according to claim 5, wherein the pixel has a charge/voltage conversion unit and which is connected to said the buried photodiode through a transfer switch.

7. (Currently amended) A sensor according to claim 1, wherein said sensor block and said signal processing block are connected via a level shift means circuit for shifting a signal level.

8. (Original) A sensor according to claim 1, wherein said signal processing block comprises an A/D conversion circuit for converting an analog signal into a digital signal.

9. (Currently amended) A sensor according to claim 8, wherein said

signal processing block comprises a signal processing ~~means~~ circuit for forming a luminance signal and a chrominance signal.

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10.-20. (Canceled)

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